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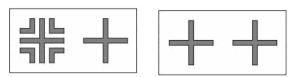
# Packaging and System Facility (PASF)

# **Packaging and Design Services Capabilities**

# 1. Wafer Dicing

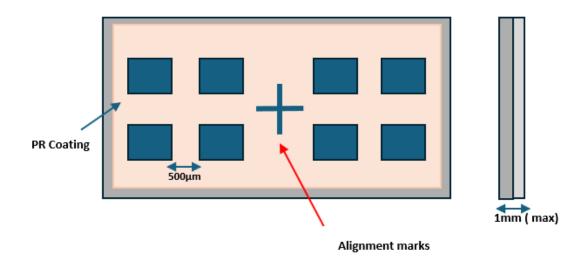
# 1.1 Automatic Dicing Saw

- i. Wafer/sample size can handle from 2 cm to 6-inch wafers.
- ii. Capable of performing both full cuts and half cuts.
- iii. Sample types: silicon wafers, ITO, STO, LNO, glass wafers and bonded wafers (Si on Si and glass on Si).
- iv. Maximum wafer/sample thickness: 1 mm.
- v. Minimum dicing sample size: 2 mm × 2 mm.
- vi. Minimum saw street between devices: 500 μm (no metallization on saw street).
- vii. Device placement on the wafer/sample must follow a uniform index.
- viii. Wafer/samples with released structures are not acceptable.
- ix. Alignment marks are mandatory on the wafer/sample.



x. The dicing side of the sample must be coated with PR (photoresist) material (maximum  $1\mu$ m thick).

Figure1: Wafer Profile for Automatic Dicing



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# 1.2 MTI Precision CNC Dicing machine

- i. Wafer/sample size can range from 2 cm to 3-inch wafers.
- ii. Allowed only fresh/unprocessed wafers.
- iii. Wafer/sample types: silicon wafers, glass wafers, ceramics and sapphires.
- iv. Maximum wafer/sample thickness: 3 mm.
- v. Minimum dicing sample size: 2 mm × 2 mm.
- vi. Minimum cut line width between devices: 500 µm (without metallization).
- vii. Device placement on the wafer/sample must follow a uniform index
- viii. Samples with released structures are not acceptable. (Patterned wafers are not allowed)
- ix. Alignment marks are not a mandatory on the dicing sample.
- x. The dicing side of the sample must be coated with PR (photoresist) material (maximum  $1\mu$ m thick).

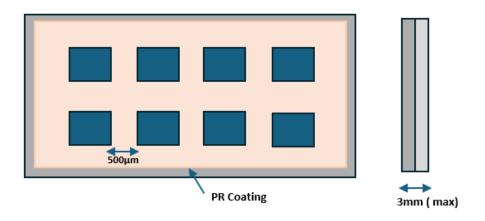


Figure 2: Wafer Profile for Manual Dicing

# 2. Wire bonding

#### 2.1 Die attachment

- i. User should provide the package (PCB with ENIG/ENPIG finish, Chip carrier, TO)
- ii. Epoxy available: (Curing Temperature as per data sheet)

H70E: Thermally conductive

H20E: Thermally and electrically conductive

H70E2: Thermally conductive

iii. Process type - manual

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#### 2.2 Wire bonder

- i. Diced devices are recommended, or devices that can fit within the package dimensions.
- ii. Bonding Type & Material:
  - Wedge bonding: 25 μm Au wire, 33 μm Al wire
  - Ball bonding: 25 μm Au wire
- iii. Minimum Bond Pad Dimension: 100 μm × 100 μm
- iv. Minimum Bond Pad Pitch: 200 μm
- v. Device Metallization: Al, Cr/Au, Ti/Pt or Ti/Au (seed layer thickness > 10 nm and metallization > 100 nm)
- vi. Bond pad surface must be free from contamination, photoresist (PR) and oxide layers.

#### 3. Parylene Deposition

- i. Substrates allowed ranging from small samples up to 4-inch wafers.
- ii. Samples: silicon wafers, glass, ceramics, metals, MEMS devices, electronic components, medical implants, polymers, plastics, and optical parts.
- iii. Parylene Type: Parylene C, Parylene N
- iv. Capable of depositing thickness: 500nm to  $5\mu m$ .
- v. Provides uniform coatings on substrates of various shapes and sizes, including non-flat samples, facilitated by a rotating sample holder.
- vi. Deposition pressure approximately 15mTorr, enabling the formation of high-quality conformal coatings.

#### 4. Hot air Oven

- i. Samples allowed for baking/curing: Silicon, glassware, metal tools, electronic components, polymers, powders, and small mechanical parts.
- ii. Internal Dimension: 30cm × 30cm × 30cm
- iii. Temperature range: 150°C to 180°C
- iv. Temperature uniformity: ± 3°C
- v. Ramp Rate: 3°C/min

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#### 5. Vacuum Oven

i. Samples allowed for baking/curing: Silicon, glassware, metal tools, electronic components, polymers, powders, and small mechanical parts.

ii. Internal Dimension: 35cm × 35cm × 35cm

iii. Vacuum Range: 5mTorr

iv. Temperature range: 25°C to 250°C

v. Temperature uniformity: ± 3°C

vi. Ramp Rate: 2°C/min

#### 6. High Power Plasma Cleaner

 Samples allowed for surface cleaning /Bonding: silicon wafers, glass, metals, polymers, ceramics, MEMS devices, and PDMS

ii. Sample size: < 65 mm

iii. Adjustable RF power: Low (8W), Medium (14W), High (40W)

iv. Vacuum range: 5mTorr

v. Gas exposure: N<sub>2</sub>, Ar, O<sub>2</sub>

vi. Gas Flow meter range: 50 mL/min

vii. Samples with greasy residues, oily films, unbaked resists or uncured polymers are not allowed

viii. Two slots for gas flow meters.

### 7. DC Probe station

i. Samples allowed with metal layer: Silicon wafers, Glass and MEMS devices

ii. Sample size: < 50 mm

iii. Probing Pad size: 100 μm

iv. Microscope Magnification: 10x - 50x

v. Micro Positioners: 6 units with magnet on/off bases

vi. Measurement Capabilities: Resistance, Inductance, Capacitance

vii. Probe tip size: 50 μm

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#### 8. Ultra Probe sonication

i. Samples allowed for dispersion: RGO, CNT, Graphene, Nanoparticles

ii. Frequency Range: Typically, 20-40 kHz

iii. Probe Tip size: 0.3mm and 18mm

iv. Power Output: Ranges from 50 W to 500 W RMS

v. Mode of operation: Continuous /Pulse Mode

vi. Probe/Tip Material: Titanium due to its durability and chemical resistance

vii. Tab/PC operation.

### 9. Centrifuge system

 Samples allowed for separation and concentration of nanoparticles, carbon nanotubes (CNTs), graphene.

ii. Maximum Speed: 10,000 RPM

iii. Speed Accuracy: ±100 RPM

iv. Maximum Tube Size: 100 mL

v. No. of. tube slot: 8 no's

#### 10. Chemical Wet bench

i. Samples allowed for cleaning: Silicon, glass, PCB, Metal components

ii. Allowed process chemicals: IPA and Acetone

iii. Support for sample dehydration and preheating processes.

iv. Ultrasonic bath cleaning for effective removal of contaminants.

v. Equipped with exhaust ventilation, chemical-resistant surfaces and splash guards for safe operation.

vi. Equipped with DI water, N<sub>2</sub> gas and CDA lines for sample cleaning.

# 11. Fibre laser marking tool

i. Materials allowed: Metals, Silicon wafers, Plastic, PCB

ii. Process: Metal shadow mask, Text engraving, Pattern transfer and QR code.

iii. Laser type: Fibre Laser (20W), 1064 nm, class 1 safety ring

iv. Marking Area: 100 × 100 mm

v. Minimum line width: 0.05mm

vi. Marking Depth: ≤ 0.3 mm

vii. Supported File Formats: DXF, BMP, JPG, DWG and EZD.

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#### 12. Helium leak tester

- i. Minimum Detectable Leak Rate: Helium (vacuum mode):  $< 5 \times 10^{-12}$  mbar·l/s
- ii. Test method: Spray Method
- iii. Measurement Range:  $1 \times 10^{-12}$  to  $1 \times 10^{-1}$  mbar·l/s
- iv. Helium Pumping Speed (vacuum mode): 2.5 l/s
- v. Flange Type: DN 25 ISO-KF
- vi. Suitable Materials for Leak Testing: Metals: Stainless steel, aluminium, copper, titanium

#### 13. Pneumatic Pressure Calibrator/controller

- i. Pressure range: up to 75 bar
- ii. Mode of calibration: Relative, Absolute
- iii. Accuracy: ±0.015% of reading
- iv. Required test port end fitting (Male): 1/4" BSP, M10X1, M14 x1.5
- v. Test Medium N<sub>2</sub> gas

# 14. Hydraulic Pressure Calibrator

- i. Pressure range:1 to 1000 bar
- ii. Mode of calibration: Relative/Gauge
- iii. Accuracy: ±0.015% of reading
- iv. Required test port end fitting (Male): 1/8, 1/4, 3/8 and ½ NPT or BSP
- v. Test Medium Hydraulic oil

#### 15. Pressure Cycle Tester

- i. Pressure range: up to 10 bar
- ii. Mode of calibration: Relative, Absolute
- iii. Test Medium: Compressed Air, N<sub>2</sub> gas
- iv. Required test port end fitting (Male): 1/2" BSP, M10X, M14 x1.5
- v. Programmable total cycles: up to 10,000
- vi. Adjustable pressure hold time



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### 16. Dynamic Pressure test (Shock Tube)

i. Shock wave pressure: 1 to 10 bar

ii. Test method: Diaphragm rupture method, Solenoid valve control method

iii. Test medium: Compressed Air, N<sub>2</sub> gas

iv. Required test port end fitting (Male): ¼" BSP, M10X1, M14 x1.5

#### 17. Climatic Test Chamber

i. Temperature Range: -60°C to +170°C

ii. Humidity Range: 10% to 90% RH (at +10°C to +95°C)

iii. Internal Dimensions: 548 × 460 × 447 mm

iv. Cooling Rate: 2.8°C/min (from +170°C to -60°C)

v. Heating Rate: 3.2°C/min (from -60°C to +160°C)

vi. Temperature Fluctuation: ±1°C

vii. Relative Humidity Fluctuation: ±3%

viii. Programmable test profiles for automated sequences

ix. Fed through access port (Dia 50mm) for taking electrical connection

#### 18. Soldering and Desoldering workstation

i. Process type: Manual hand soldering and desoldering

ii. PCB: Rigid, Flex

iii. PCB board dimensions: 80 mm x 80mm

iv. Small PCBs are preferred in panel

v. Component Type: SMD (0603,0805,1206), QFN, SSOP, SOIC

vi. Support only for proto unit test and development units.

vii. A stencil is recommended for panels or larger PCBs

### 19. FDM \_ 3D printing

i. Print Filament Material: PLA, ABS

ii. Build part dimension: 180mm x 180mm x 180mm

iii. Layer resolution: 0.16mm to 0.4mm

iv. Required file format: STL file



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### 20. Embedded Design Services

#### Hardware design:

Project architecture design, schematic design (Analog, digital, mixed signals, power management), component selection, Custom board design, PCB layout-multi layer, multi-board design, impedance matching, differential pair analysis, and prototyping.

#### • Firmware development:

Low-level software development for microcontroller (STM32, Analog devices, TI, ATmega) systems (Single, dual-core, multi-controller designs). Device drivers – SPI, I2C, UART, RS232, RS485, RTOS.

# • Software development:

Embedded software development using Python, Visual Code Studio, and front-end development.

#### System integration:

Seamless hardware, firmware, software, and mechanical components integration.

#### Testing and validation:

Rigorous testing procedures to ensure product quality and reliability. Active and passive burn-in testing, temperature cycling, and humidity testing.